### **TGA2576-2-FL** 2.5–6.0 GHz 40 W GaN Power Amplifier

#### **Product Overview**

Qorvo's TGA2576-2-FL is a wideband power amplifier fabricated on Qorvo's proven 0.25um GaN on SiC production technology. Operating from 2.5 to 6 GHz, the TGA2576-2-FL achieves 40W of saturated output power, greater than 36% power-added efficiency and 29dB small signal gain.

For ideal thermal management and handling, the TGA2576-2-FL is offered in a CuW-based flanged packaged and can operate in both CW and pulsed modes.

Both RF ports are fully matched to  $50\Omega$ , the TGA2576-2-FL is ideally suited to support a variety of commercial and defense related applications.

Lead-free and RoHS compliant.



#### **Key Features**

- Frequency Range: 2.5 to 6 GHz
- P<sub>SAT</sub>: 46.5 dBm (P<sub>IN</sub> = 26 dBm)
- PAE: 36% (P<sub>IN</sub> = 26 dBm)
- Small Signal Gain: 29 dB
- Bias: Pulse  $V_D = 30 V$ ,  $I_{DQ} = 1.55 A$
- Dimensions: 11.4 x 17.3 x 3.0 mm

Performance is typical across frequency. Please reference electrical specification table and data plots for more details.

#### **Functional Block Diagram**



#### **Applications**

- Communications
- Electronic Warfare
- Test Instrumentation
- EMC Amplifier

#### **Ordering Information**

Part No.	Description
TGA2576-2-FL	2.5–6.0 GHz 40 Watt GaN Power Amplifier
TGA2576-2-FL EVB	Evaluation Board

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#### **Absolute Maximum Ratings**

Parameter	Rating		
Drain Voltage (V <sub>D</sub> )	40 V		
Gate Voltage (V <sub>G</sub> )	-8 to 0 V		
Drain Current (I <sub>D</sub> )	5000 mA		
Gate Current (I <sub>G</sub> )	See plot, page 6		
Power Dissipation (P <sub>DISS</sub> )	93 W		
RF Input Power, CW, 50 $\Omega$ , T = 25 °C	28 dBm		
Soldering Temperature (leads)	260 °C		
Storage Temperature	−40 to +150 °C		

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

#### **Recommended Operating Conditions**

Parameter	Min		
Drain Voltage (V <sub>D</sub> )	30 V		
Drain Current (I <sub>DQ</sub> )	1550 mA		
Drain Current (ID_DRIVE)	4300 mA		
Operating Temperature	−40 to +85 °C		

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

#### **Electrical Specifications**

Parameter	Min	Тур	Max	Units
Operational Frequency Range	2.5		6.0	GHz
Small Signal Gain		29		dB
Output Power @ Saturation (Pin = 26 dBm)		46.5		dBm
Power-Added Efficiency (midband; Pin = 26 dBm)		36		%
Gate Leakage ( $V_D = 10 \text{ V}, V_G = -3.7 \text{ V}$ )	-20		-0.0001	mA
Small Signal Gain Temperature Coefficient		-0.02		dB/°C
Output Power Temperature Coefficient		-0.02		dBm/°C

#### Notes:

Test conditions unless otherwise noted: T=25 °C,  $V_D$  = 30 V,  $I_{DQ}$  = 1550 mA, CW operation

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#### **Performance Plots – Large Signal**

Test conditions unless otherwise noted: T=25 °C, V<sub>D</sub> = 30 V, I<sub>DQ</sub> = 1550 mA, CW



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Test conditions unless otherwise noted: T=25 °C, V<sub>D</sub> = 30 V, I<sub>DQ</sub> = 1550 mA, CW



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### Performance Plots – Small Signal

Test conditions unless otherwise noted: T=25 °C, V<sub>D</sub> = 30 V, I<sub>DQ</sub> = 1550 mA



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#### **Thermal and Reliability Information**

Parameter	Test Conditions	Value	Units
Thermal Resistance ( $\theta_{JC}$ ) <sup>(1)</sup>	T <sub>BASE</sub> = 85 °C, V <sub>D</sub> = 30 V, I <sub>DQ</sub> = 1550 mA, I <sub>D_Drive</sub> =	1.245	°C/W
Channel Temperature, T <sub>CH</sub> (Under RF Drive) <sup>(2)</sup>	3600 mA, P <sub>OUT</sub> = 46 dBm, P <sub>DISS</sub> = 72 W	174.6	°C

#### Notes:

1. Thermal resistance referenced to the back of the package (T = 85 °C).

2. Refer to the following document: GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates

#### **Dissipated Power and Maximum Gate Current**





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#### **Applications Information**



#### Notes:

- 1.  $V_G$  can be biased from both sides (Pins 1 and 5)
- 2.  $V_D$  must be biased from both sides (Pins 6 and 10)
- 3. C7 and C8 may be removed for pulsed drain operation.

#### **Bias-Up Procedure**

- 1. Set power supply: I<sub>D</sub> limit to 5 A, I<sub>G</sub> limit to 10 mA
- 2. Apply -5.0 V to V<sub>G</sub> (for pinch-off)
- 3. Increase V<sub>D</sub> to +30 V; Ensure  $I_{DQ}$  < 10 mA
- 4. Adjust V<sub>G</sub> more positive until  $I_{DQ}$  = 1550 mA
- 5. Apply RF signal

#### **Bias-Down Procedure**

- 1. Turn off RF signal
- 2. Reduce V<sub>G</sub> to -5.0 V; Ensure I<sub>DQ</sub> ~ 0 mA
- 3. Reduce  $V_D$  to 0 V
- 4. Turn off V<sub>G</sub> supply



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#### **Evaluation Board (EVB) Layout Assembly**



#### **Bill of Materials**

Reference Des.	Value	Description	Manuf.	Part Number
C1 - C4	0.1 µF	Cap, 0603, 50 V, 10%, X7R	Various	
C5 – C8	1 µF	Cap, 1206, 50 V, 10%, X7R	Various	
J1, J2	2.92 mm	Female End Launch Connector	Southwest Microwave	1092-01A-5

Note: Can remove C7, C8 for pulsed operation

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#### **Mechanical Information and Bond Pad Description**

#### **Package Lead Description**

Pad No.	Symbol	Description
1, 5	V <sub>G</sub>	Gate voltage (1)
2, 4, 7, 9	NC	No internal connection; may be grounded or left open on PCB
3	RFIN	RF Input; matched to 50 $\Omega$ ; DC shorted to ground
6, 10	VD	Drain voltage <sup>(2)</sup>
8	RFOUT	RF Output; matched to 50 $\Omega$ ; DC shorted to ground
-	Package Base	RF and DC ground

#### Notes:

Marking:

Notes:

Batch ID:

Bias network is required; must be biased from both sides (Pins 1 and 5); see Application Circuit on page 7 1.

2. Bias network is required; must be biased from both sides (Pins 6 and 10); see Application Circuit on page 7



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#### **Assembly Notes**

**Component Installation** 

- 0-80 screws are recommended for mounting the TGA2576-2-FL to the board.
- To improve the thermal and RF performance, Qorvo recommends the following: Apply either Arctic Silver 5 thermal compound or a 2-4 mil thick HeatSpring indium shim between the package and the heat sink
- Apply solder to each pin of the TGA2576-2-FL

The package should not be subjected to conventional reflow processes. The use of no-clean solder to avoid washing after soldering is highly recommended.

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#### Handling Precautions

Parameter	Rating	Standard		
ESD-Human Body Model (HBM)	1B	ESDA / JEDEC JS-001-2012	R.	Caution! ESD-Sensitive Device
MSL-Moisture Sensitivity Level	NA			

#### **Solderability**

The component leads should be manually soldered, and the package should not be subjected to conventional reflow processes. Soldering of the component leads is compatible with the latest version of J-STD-020, lead-free solder, 260 °C. The use of no-clean solder to avoid washing after soldering is highly recommended.

#### **RoHS Compliance**

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>0<sub>2</sub>) Free
- PFOS Free
- SVHC Free

#### **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations:

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